

# 4V Drive Nch+Pch MOSFET

# **SH8M2**

#### Structure

Silicon N-channel / P-channel MOSFET

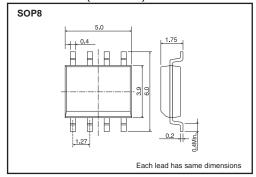
#### ● Features

- 1) Low on-resistance.
- 2) Built-in G-S protection diode.
- 3) Small surface mount package (SOP8).

#### Application

Power switching, DC / DC converter.

#### ●Dimensions (Unit : mm)



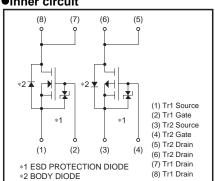
# Packaging specifications

	Package	Taping
Type	Code	TB
	Basic ordering unit (pieces)	2500
SH8M2		0

#### ●Absolute maximum ratings (Ta=25°C)

Parameter		Cumbal	Lin	Unit	
		Symbol	Tr1: N-ch Tr2: P-ch		Offic
Drain-source voltage		V <sub>DSS</sub>	30	-30	V
Gate-source voltage	Gate-source voltage		±20	±20	V
Drain current	Continuous	lσ	±3.5	±3.5	Α
	Pulsed	I <sub>DP</sub> *1	±14	±14	Α
Source current	Continuous	Is	1.6	-1.6	Α
(Body diode)	Pulsed	Isp*1	14	-14	Α
Total power dissipation		P <sub>D</sub> *2	2.0		W / TOTAL
Channel temperature		Tch	150		°C
Storage temperature		Tstg	-55 to +150		°C

#### ●Inner circuit



<sup>\*1</sup> Pw≤10μs, Duty cycle≤1% \*2 Mounted on a ceramic board.

SH8M2 Data Sheet

N-ch

# ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	-	_	±10	μΑ	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V
Drain-source breakdown voltage	V <sub>(BR)</sub> DSS	30	_	_	V	I <sub>D</sub> = 1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	IDSS	-	-	1	μА	Vps= 30V, Vgs=0V
Gate threshold voltage	V <sub>GS (th)</sub>	1.0	_	2.5	V	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA
Otatio Indiana and the		-	59	83	mΩ	I <sub>D</sub> = 3.5A, V <sub>GS</sub> = 10V
Static drain-source on-state resistance	R <sub>DS (on)</sub> *	-	93	130	mΩ	I <sub>D</sub> = 3.5A, V <sub>GS</sub> = 4.5V
resistance		-	107	150	mΩ	ID= 3.5A, VGS= 4V
Forward transfer admittance	Y <sub>fs</sub> *	2.0	_	_	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 3.5A
Input capacitance	Ciss	-	140	_	pF	V <sub>DS</sub> = 10V
Output capacitance	Coss	-	45	_	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	Crss	-	30	_	pF	f=1MHz
Turn-on delay time	t <sub>d (on)</sub> *	_	6	_	ns	Vpp≒ 15V
Rise time	tr *	-	6	_	ns	ID= 1.75A
Turn-off delay time	t <sub>d (off)</sub> *	-	17	-	ns	Vgs= 10V RL= 8.57Ω
Fall time	t <sub>f</sub> *	-	4	_	ns	R <sub>G</sub> =10Ω
Total gate charge	Qg *	1	2.5	3.5	nC	V <sub>DD</sub> ≒15V, V <sub>GS</sub> =5V
Gate-source charge	Q <sub>gs</sub> *	_	0.8	_	nC	I <sub>D</sub> = 3.5A
Gate-drain charge	Q <sub>gd</sub> *	-	0.8	-	nC	$R_L=4.29\Omega$ , $R_G=10\Omega$

<sup>\*</sup>Pulsed

# ●Body diode characteristics (Source-Drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp*	_	_	1.2	V	Is= 6.4A, Vgs=0V

<sup>\*</sup>Pulsed

SH8M2 Data Sheet

P-ch ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	_	_	±10	μΑ	V <sub>GS</sub> = ±20V, V <sub>DS</sub> =0V
Drain-source breakdown voltage	V <sub>(BR)</sub> DSS	-30	_	_	V	I <sub>D</sub> = -1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	I <sub>DSS</sub>	-	_	-1	μА	V <sub>DS</sub> = -30V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS (th)</sub>	-1.0	_	-2.5	V	$V_{DS}=-10V$ , $I_{D}=-1mA$
Otatio Indiana and at a		_	65	90	mΩ	I <sub>D</sub> = -3.5A, V <sub>G</sub> S= -10V
Static drain-source on-state resistance	RDS (on)*	_	100	140	mΩ	I <sub>D</sub> = -1.75A, V <sub>G</sub> s= -4.5V
resistance		_	120	165	mΩ	I <sub>D</sub> = -1.75A, V <sub>G</sub> S= -4V
Forward transfer admittance	Y <sub>fs</sub> *	1.8	-	_	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -1.75A
Input capacitance	Ciss	-	490	_	pF	V <sub>DS</sub> = -10V
Output capacitance	Coss	_	110	_	pF	Vgs= 0V
Reverse transfer capacitance	Crss	_	75	_	pF	f=1MHz
Turn-on delay time	t <sub>d (on)</sub> *	-	10	_	ns	V <sub>DD</sub> ≒ −15V
Rise time	tr *	-	15	_	ns	ID= -1.75A
Turn-off delay time	td (off) *	_	35	_	ns	$V_{GS} = -10V$ $R_{L} = 8.57\Omega$
Fall time	t <sub>f</sub> *	_	10	_	ns	R <sub>G</sub> = 10Ω
Total gate charge	Qg *	_	5.5	7.7	nC	V <sub>DD</sub> ≒-15V, V <sub>GS</sub> =-5V
Gate-source charge	Q <sub>gs</sub> *	-	1.5	-	nC	I <sub>D</sub> = -3.5A
Gate-drain charge	Q <sub>gd</sub> *	_	2.0	_	nC	$RL=4.29\Omega$ , $RG=10\Omega$

<sup>\*</sup>Pulsed

# ●Body diode characteristics (Source-Drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp*	_	_	-1.2	V	I <sub>S</sub> = -1.6A, V <sub>G</sub> S=0V

<sup>\*</sup>Pulsed

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